## SURFACE MOUNT SILICON DUAL P-CHANNEL ENHANCEMENT-MODE MOSFET



### SOT-563 CASE

### **APPLICATIONS:**

- Load switch/Level shifting
- · Battery charging
- · Boost switch
- Electro-luminescent backlighting

<b>Central</b>
Semiconductor Corp.

www.centralsemi.com

## **DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMLDM5757 consists of dual silicon P-Channel enhancement-mode MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low rDS(ON) and low threshold voltage.

### **MARKING CODE: 77C**

### **FEATURES:**

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low r<sub>DS(ON)</sub>
- Low threshold voltage
- · Logic level compatible
- Small, SOT-563 surface mount package

MAX

• Complementary dual N-Channel device: CMLDM3737

MAXIMUM RATINGS: (TA=25°C)	SYMBOL		UNITS
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	8.0	V
Continuous Drain Current (Steady State)	$I_{D}$	430	mA
Maximum Pulsed Drain Current (tp=10µs)	$I_{DM}$	750	mA
Power Dissipation (Note 1)	$P_{D}$	350	mW
Power Dissipation (Note 2)	$P_{D}$	300	mW
Power Dissipation (Note 3)	$P_{D}$	150	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	-65 to +150	°C
Thermal Resistance (Note 1)	$\Theta_{\sf JA}$	357	°C/W

ELECTRICAL (	CHARACTERISTICS PER	R TRANSISTOR: (T <sub>A</sub> =25°C)
SYMBOL	TEST CONDITIONS	MIN
lagge, lagge	VGS=4.5V. VDS=0	

IGSSF, IGSSF	$_{\rm R}$ V <sub>GS</sub> =4.5V, V <sub>DS</sub> =0		2.0	μΑ
I <sub>DSS</sub>	$V_{DS}$ =16V, $V_{GS}$ =0		1.0	μΑ
$BV_{DSS}$	$V_{GS}=0$ , $I_D=250\mu A$	20		V
V <sub>GS(th)</sub>	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	0.45	1.0	V
$V_{SD}$	V <sub>GS</sub> =0, I <sub>S</sub> =350mA		1.2	V
rDS(ON)	$V_{GS}$ =4.5V, $I_D$ =430mA		0.9	Ω
rDS(ON)	$V_{GS}$ =2.5V, $I_D$ =300mA		1.2	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.8V, I <sub>D</sub> =150mA		2.0	Ω
C <sub>rss</sub>	$V_{DS}$ =16V, $V_{GS}$ =0, f=1.0MHz		20	pF
C <sub>iss</sub>	$V_{DS}$ =16V, $V_{GS}$ =0, f=1.0MHz		175	pF
C <sub>oss</sub>	$V_{DS}$ =16V, $V_{GS}$ =0, f=1.0MHz		30	pF

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²

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UNITS

<sup>(2)</sup> FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm<sup>2</sup>

<sup>(3)</sup> FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²



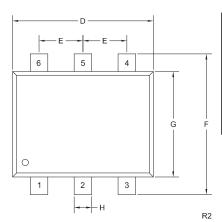


**ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued:** (T<sub>A</sub>=25°C)

SYMBOL	TEST CONDITIONS	TYP	NITS
$Q_{g(tot)}$	$V_{DS}$ =10V, $V_{GS}$ =4.5V, $I_{D}$ =200mA	1.2	nC
Qgs	$V_{DS}$ =10V, $V_{GS}$ =4.5V, $I_{D}$ =200mA	0.24	nC
$Q_{gd}$	$V_{DS}$ =10V, $V_{GS}$ =4.5V, $I_{D}$ =200mA	0.36	nC
ton	$V_{DD}$ =10V, $V_{GS}$ =4.5V, $I_{D}$ =215mA, $R_{G}$ =10 $\Omega$	38	ns
t <sub>off</sub>	$V_{DD}$ =10V, $V_{GS}$ =4.5V, $I_{D}$ =215mA, $R_{G}$ =10 $\Omega$	48	ns

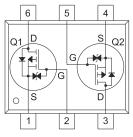
## **SOT-563 CASE - MECHANICAL OUTLINE**





DIMENSIONS				
	INCHES		MILLIM	ETERS
SYMBOL	MIN	MAX	MIN	MAX
Α	0.0027	0.007	0.07	0.18
В	0.008		0.20	
С	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
Е	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
Н	0.006	0.012	0.15	0.30
SOT-563 (REV: R2)				

# PIN CONFIGURATION



### **LEAD CODE:**

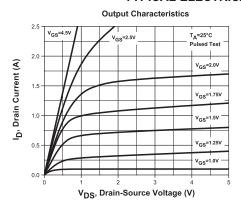
- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

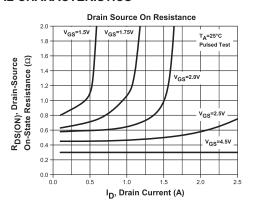
**MARKING CODE: 77C** 

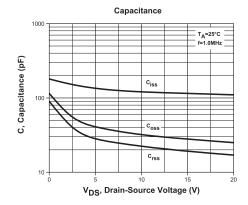
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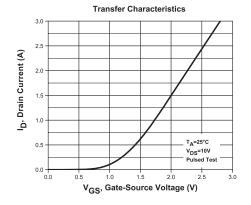


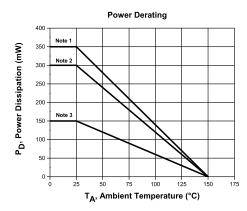
# TYPICAL ELECTRICAL CHARACTERISTICS











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## SURFACE MOUNT SILICON DUAL P-CHANNEL ENHANCEMENT-MODE MOSFET



#### **SERVICES**

- · Bonded Inventory
- · Custom Electrical Screening
- Custom Electrical Characteristic Curves
- SPICE Models
- Custom Packaging
- Package Base Options
- Custom Device Development/Multi Discrete Modules (MDM™)
- · Bare Die Available for Hybrid Applications

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